

General Description

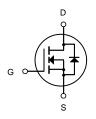
The NTTFS5C471NL use advanced SGT MOSFET technology to provide low RDS(ON), low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness and suitable.

DFN3X3-8L

General Features

V_{DS} =40V I_D =60 A

 $R_{DS(ON)}$ < 8.5m Ω @ V_{GS} =10V



N-Channel MOSFET

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NTTFS5C471NL	DFN3X3-8L	HXY MOSFET	5000

Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	VDS	40	V
Gate source voltage	VGS	±20	V
Continuous drain current ¹⁾	ID	60	Α
Pulsed drain current ²⁾	ID, pulse	130	А
Power dissipation ³⁾	P _D	39	W
Single pulsed avalanche energy ⁵⁾	EAS	48	mJ
Operation and storage temperature	Tstg, Tj	-55 to 150	°C
Thermal resistance, junction-case	RθJC	3.2	°C/W
Thermal resistance, junction-ambient ⁴⁾	RθJA	60	°C/W

N-SGT Enhancement Mode MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V
D- avaus	Static Drain-Source On-Resistance ²	V_{GS} =10V , I_D =12A		6.9	8.5	mΩ
Rds(on)		V _{GS} =4.5V , I _D =10A		10.0	15	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.35		3	V
	Drain-Source Leakage Current	V _{DS} =32V , V _{GS} =0V , T _J =25°C			1	uA
I _{DSS}		V _{DS} =32V , V _{GS} =0V , T _J =55°C			5	
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			5.8		nC
Qgs	Gate-Source Charge	V _{DS} =20V , V _{GS} =4.5V , I _D =12A		3		
Q _{gd}	Gate-Drain Charge			1.2		
T _{d(on)}	Turn-On Delay Time			14.3		
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		5.6		no
$T_{d(off)}$	Turn-Off Delay Time	I _D =1A		20		ns
T _f	Fall Time			11		
Ciss	Input Capacitance			690		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		193		pF
C_{rss}	Reverse Transfer Capacitance			38		
ls	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			60	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1	٧

Note:

^{1.}The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper. 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%

^{3.}The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =31A 4.The power dissipation is limited by 150°C junction temperature

^{5.}The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

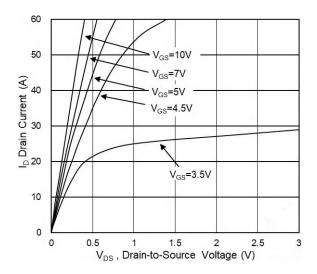


Fig.1 Typical Output Characteristics

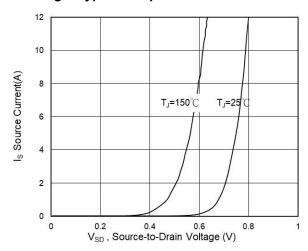


Fig.3 Source Drain Forward Characteristics

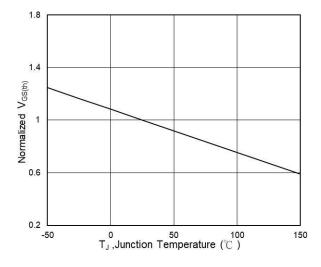


Fig.5 Normalized $V_{GS(th)}$ vs T_J

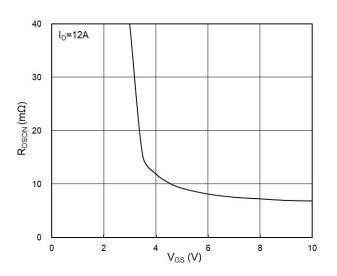


Fig.2 On-Resistance vs G-S Voltage

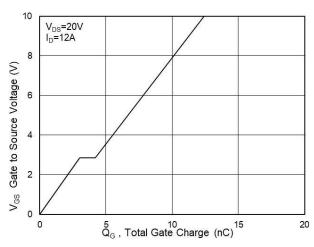


Fig.4 Gate-Charge Characteristics

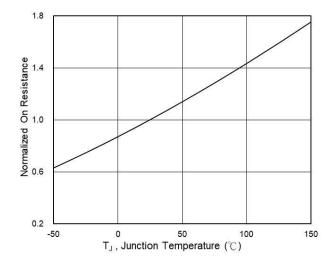
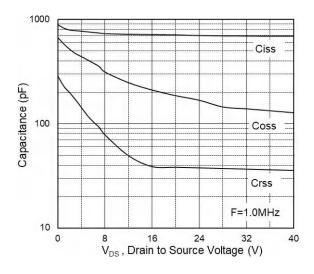


Fig.6 Normalized R_{DSON} vs T_J



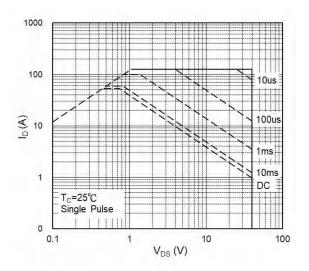
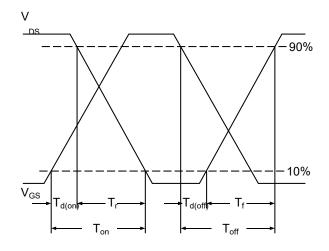


Fig.7 Capacitance Fig.8 Safe Operating Area Normalized Thermal Response (R⊎c) DUTY=0.5 0.3 0.1 0.05 P_{DM} 0.02 0.01 $D = T_{ON}/T$ $T_J peak = T_C + P_{DM} x R_{\theta JC}$ SINGLE PULSE 0.01 0.00001 0.0001 0.001 0.01 0.1 t, Pulse Width (s)

Fig.9 Normalized Maximum Transient Thermal Impedance



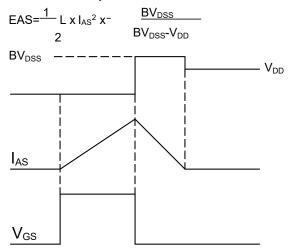
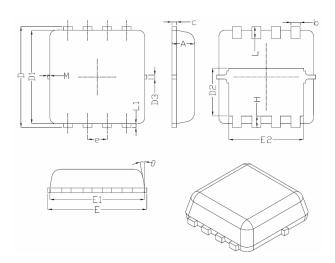


Fig.11 Unclamped Inductive Waveform

DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters			
	Min.	Nom.	Max.	
A	0.70	0.75	0.80	
b	0.25	0.30	0.35	
С	0.10	0.15	0.25	
D	3.25	3.35	3.45	
D1	3.00	3.10	3.20	
D2	1.48	1.58	1.68	
D3	-	0.13	-	
E	3.20	3.30	3.40	
E1	3.00	3.15	3.20	
E2	2.39	2.49	2.59	
e	0.65	BSC		
Н	0.30	0.39	0.50	
L	0.30	0.40	0.50	
L1	-	0.13	-	
M	*	*	0.15	
θ		10 [°]	12 [°]	



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